

EE 434

Lecture 32

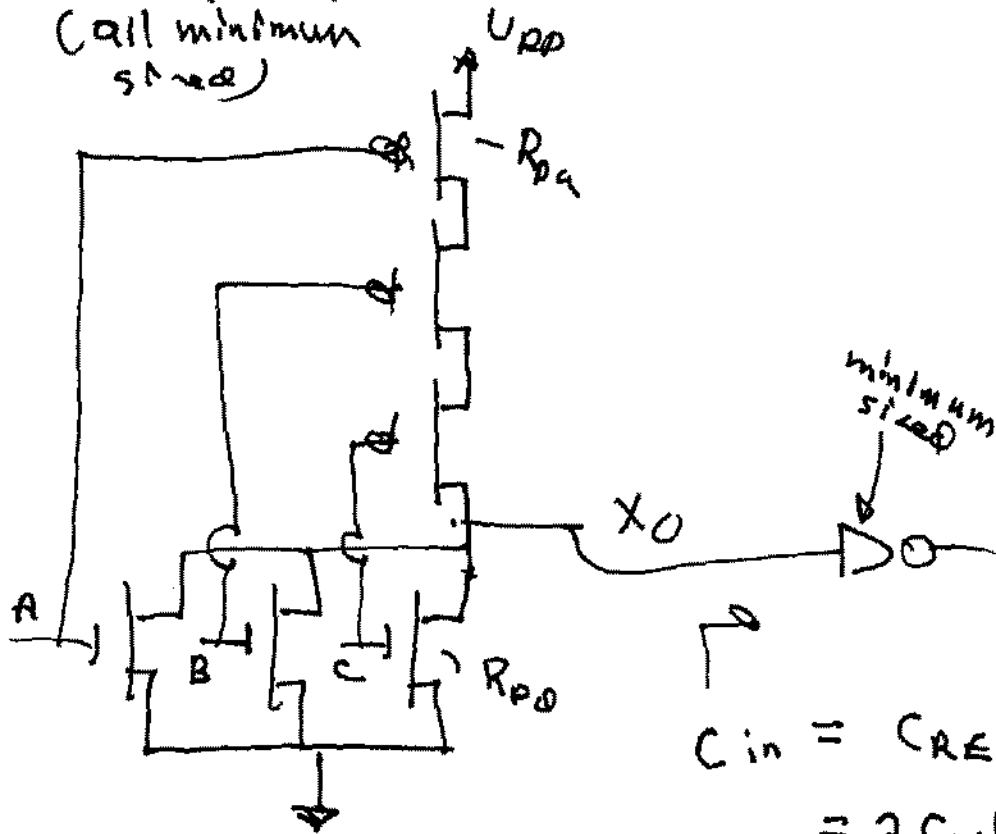
Multiple Input Logic Gates

# Review from last time

- for equal rise & fall times,  $\frac{\omega_p}{\omega_n} = \frac{\mu_n}{\mu_p}$
- no improvements nor degradations in speed compared to minimum device sizing strategy
  - - higher  $C_{in}$  (by 2x)
  - - higher dynamic power dissipation
  - - more area
  - - more design complexity
- Equal rise/fall structures widely used.

# Multiple Input Gates

Example:  
(all minimum sized)



3-input NOR

$$C_{in} = C_{REF} = 2C_{ox}W_{min}L_{min}$$

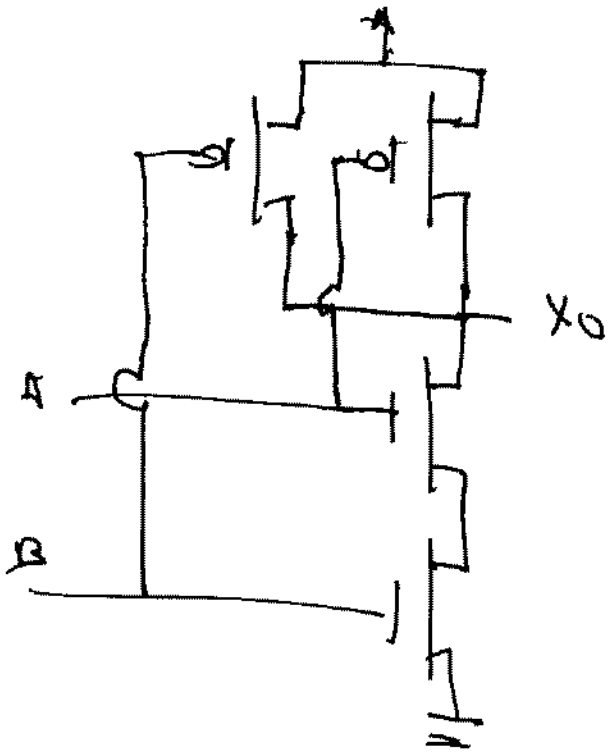
$$t_{HL} = C_{REF} R_{pa} \rightarrow \text{worst case}$$

$$t_{LH} = C_{REF} (3R_{pn})$$

$$= 9C_{REF} R_{pd} \quad \text{for } \frac{W_n}{W_p} = 3$$

Note:  $t_{LH}$  is really slow with minimum sizing strategy if # inputs is large.

Example (all minimum sized)



2-input NAND

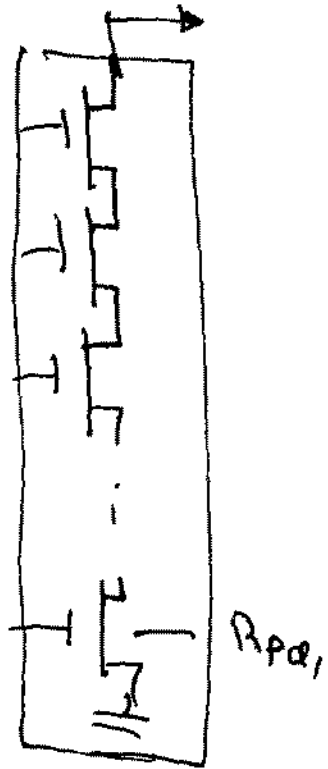
$$t_{HL} = C_{REF}(2R_{PE})$$

$$t_{LH} = C_{REF}(3R_{PE})$$

worst case

# Multiple Input NAND Gates

$P_{\phi}$ :



$$R_{p\phi} = n R_{p\phi_1} = R_{p\phi n}$$

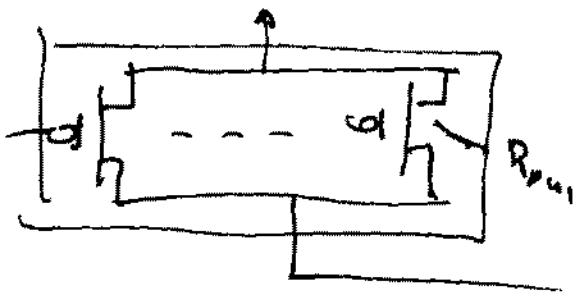
$$\therefore R_{p\phi_1} = \frac{R_{p\phi n}}{n}$$

$$\therefore L_1 = L_{min}$$

$$W_1 = n W_{min}$$

$$FI = 3C_{ox}W_{min}L_{min} + n C_{ox}W_{min}L_{min}$$

$$FI = (3+n)C_{ox}W_{min}L_{min}$$



$$R_{p\phi} = R_{p\phi_1}$$

$$\therefore L_p = L_{min}$$

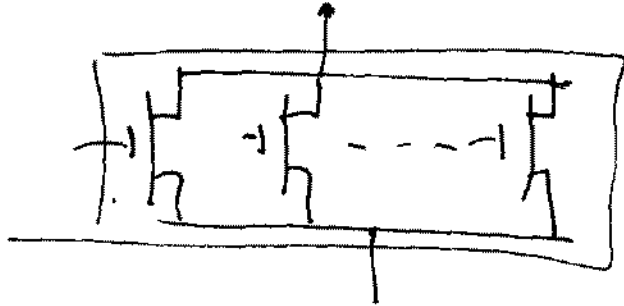
$$W_p = W_{min} \cdot 3$$

$$FI = \frac{3+n}{4} C_{REF}$$

Sizing for equal rise & fall times (equal to that of next member)

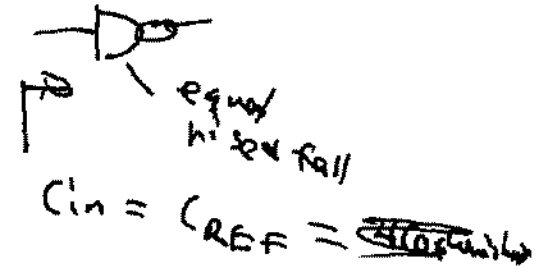
multiple-input NOR

PD:



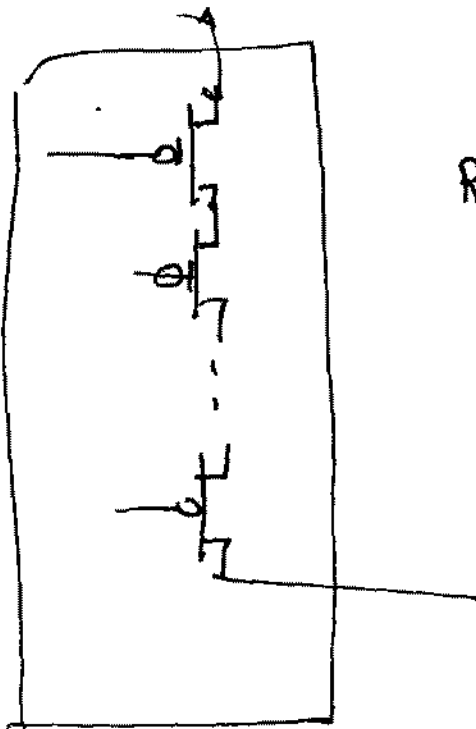
$$W = W_{min}$$

$$L = L_{min}$$



$$C_{REF} = 4/3 W_{min} L_{min}$$

PU:



$$R_{pueq} = n (3 R_{pd}) \text{ if minimum sized}$$

$$R_{pu} = R_{pd}$$

$$R_{on} = \frac{R_{pd}}{n}$$

$$L = L_{min}$$

$$W = 3n W_{min}$$

$$FI = (3n W_{min} L_{min} + W_{min} L_{min}) C_p$$

$$FI = (3n + 1) W_{min} L_{min} C_p$$

- For  $I_n$  increases

$$FI = \frac{3n+1}{4} C_{REF}$$

- Area gets large
- Layout dependent upon n sizing

$$\text{NAND: } F_I = \left( \frac{3+n}{4} \right) C_{REF}$$

$$\text{NOR: } F_I = \left( \frac{3n+1}{4} \right) C_{REF}$$

Observe: Capacitance loading presented by NOR gates much larger than that due to NAND gates if  $n$  is large

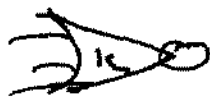
Oven drive (strength relative to a fresh inverter)



$$W_n = K W_{min}$$

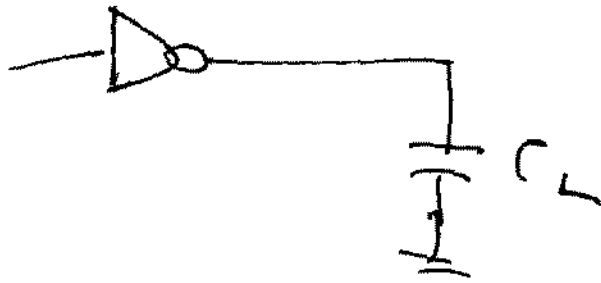
$$L_n = L_p = L_{ntn}$$

$$W_p = K (3W_{min})$$

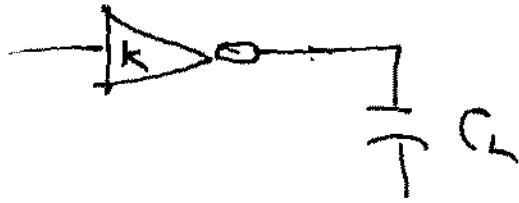


} widths of all devices  
are scaled by a factor  
of  $K$  relative to that  
of the nonscaled device.



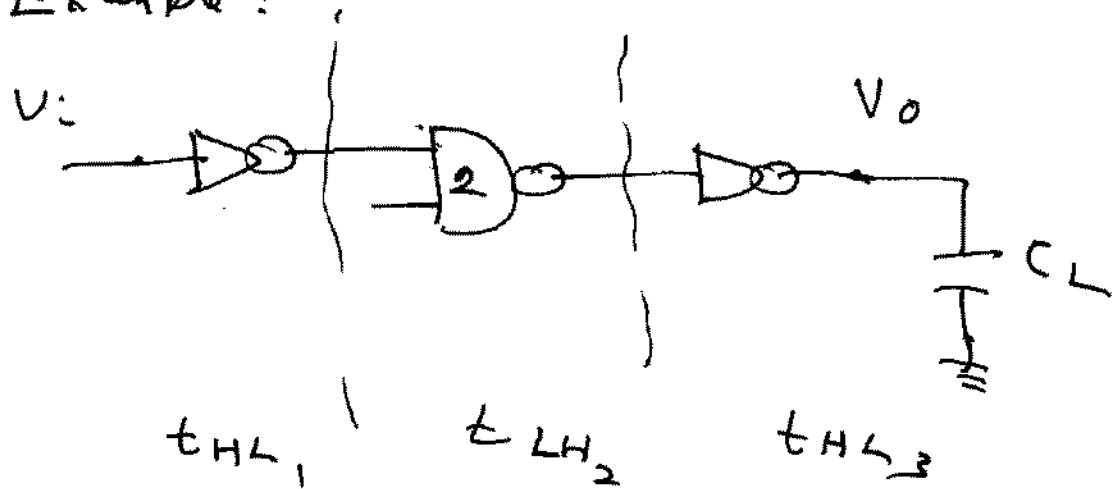


$$t_{HL} = t_{REF} \left( \frac{C_{LOAD}}{C_{REF}} \right)$$



$$t_{HL} = \frac{t_{REF}}{K} \left( \frac{C_{LOAD}}{C_{REF}} \right)$$

Example!



$$t_{HL}^1 = t_{HL1} + t_{LH2} + t_{HL3}$$

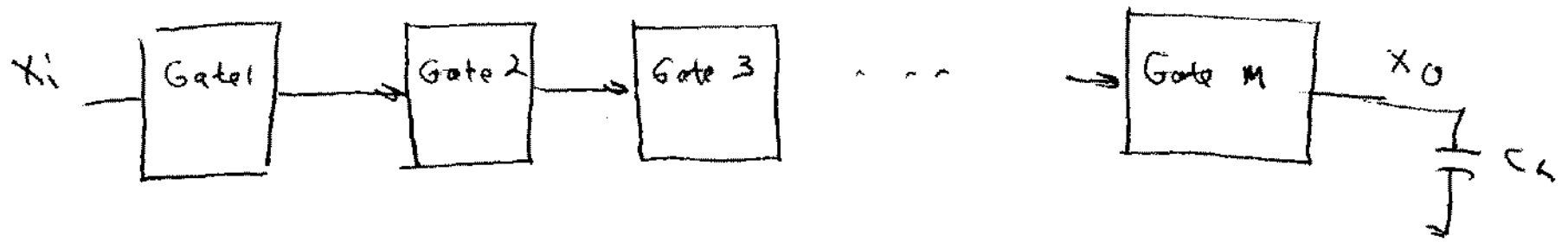
$$t_{HL1} = t_{REF} \left( \frac{C_{L1}}{C_{REF}} \right) = t_{REF} (2) \left( \frac{3+2}{4} \right) = \frac{5}{2} t_{REF}$$

$$t_{LH2} = \frac{t_{REF}}{2} \frac{C_{L2}}{C_{REF}} = t_{REF} \left( \frac{1}{2} \right)$$

$$t_{HL3} = t_{REF} \left( \frac{C_L}{C_{REF}} \right)$$

$$\therefore t_{HL}^1 = \left( \frac{5}{2} + \frac{1}{2} + \frac{C_L}{C_{REF}} \right) t_{REF}$$

# Calculating Delay in Combinational Logic Circuits - A Summary



1) Partition a delay path of interest into a chain of individual gates, (assume number is  $M$ ).

2) Determine  $FI_k$ ,  $OD_k$

$$t = \sum_{k=1}^M t_{dk}$$

where  $t$  is the overall propagation delay ( $t_{HL} + t_{LH}$ ) and  $t_{dk}$  is the propagation delay of stage  $k$

$$t_{\alpha k} = \frac{t_{REF} FI_{k+1}}{OD_k}$$

where  $FI_k = \frac{C_{ink}}{C_{REF}}$  and  $2 \leq k \leq M$

$$FI_{M+1} = \frac{C_L}{C_{REF}}$$

$$\therefore t = \left( \sum_{k=1}^M \frac{FI_{k+1}}{OD_k} \right) t_{REF}$$